

PJE260N02

N-Channel, 20V, 0.78A, Small Signal MOSFET

FEATURES

- Supper high density cell design for extremely low Rds(on)
- Exceptional ON resistance and maximum DC current capability
- Driver: Relays, Solenoids, Lamps, Hammers
- Power supply converters circuit
- Load/Power Switching for potable device
- Lead free in comply with EU RoHS 2002/95/EC directives.
- Green molding compound as per IEC61249 Std. . (Halogen Free)

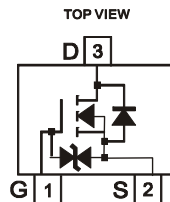
MECHANICAL DATA

Case : SOT-523 plastic

Terminals : Solderable per MIL-STD-750, Method 2026

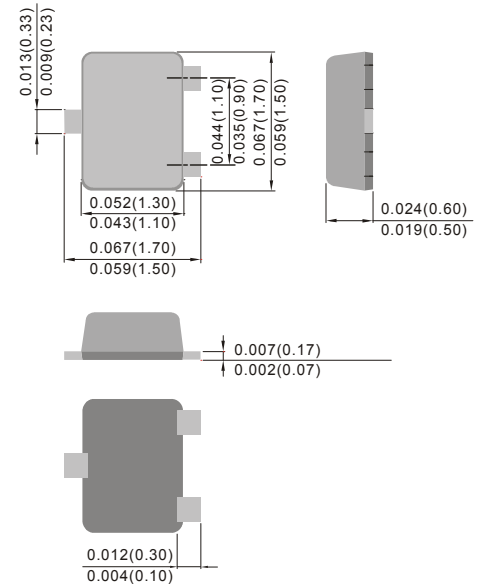
Approx Weight : 0.002 grams

Marking : 26



SOT-523

Unit : Inch(mm)



Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Limit	Units
Drain-Source Voltage	V _{DS}	20	V
Gate-Source Voltage	V _{GS}	±6	V
Continuous Drain Current (Note1)	I _D	0.78	A
Pulsed Drain Current	I _{DM}	2.34	A
Maximum Power Dissipation (Note1)	P _D	0.22	W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C
Junction-to Ambient Thermal Resistance (Note1)	R _{θJA}	576	°C / W

NOTE : 1.Mounted on min. pad FR-4 PCB.

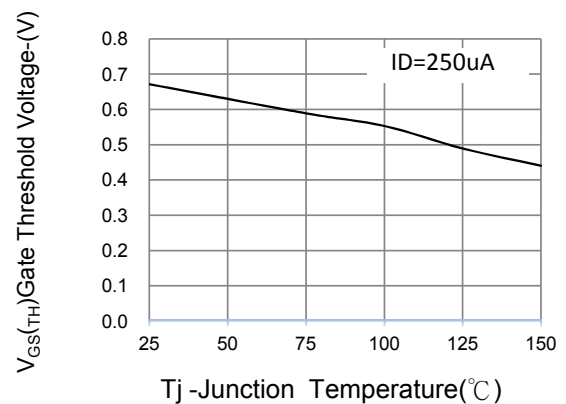
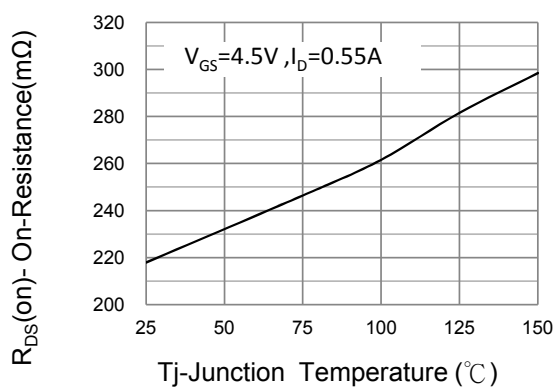
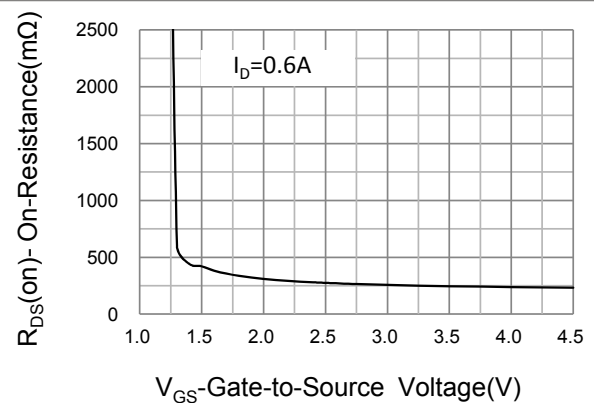
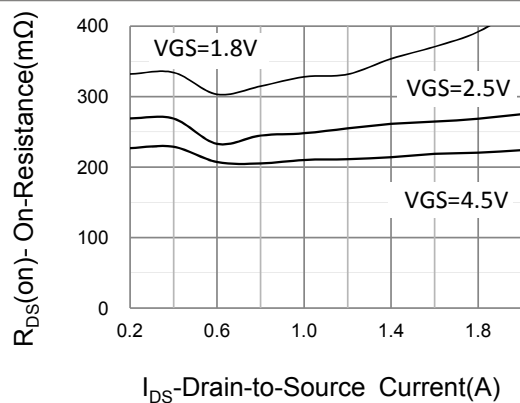
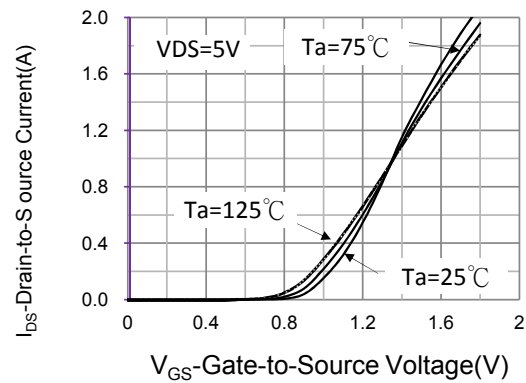
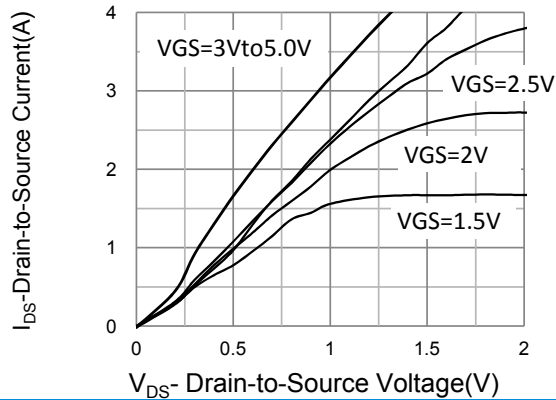
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Electronics Characteristics

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
Static						
Drain-to-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	20	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=20V, V_{GS}=0V$	-	-	1	μA
Gate-to-source Leakage Current	I_{GSS}	$V_{DS}=0V, V_{GS}=\pm 5V$	-	-	± 5	μA
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	0.45	0.67	1	V
Drain-to-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=4.5V, I_D=0.55A$	-	240	260	m Ω
		$V_{GS}=2.5V, I_D=0.45A$	-	270	310	
		$V_{GS}=1.8V, I_D=0.35A$	-	335	380	
		$V_{GS}=1.5V, I_D=0.1A$	-	400	1100	
Diode Forward Voltage	V_{SD}	$V_{GS}=0V, I_S=0.35A$	0.5	0.85	1	V
Dynamic						
Total Gate Charge	Q_g	$V_{GS}=-4.5V, V_{DS}=-10V, I_D=0.55A$	-	1.37	-	nC
Gate-Source Charge	Q_{gs}		-	0.17	-	
Gate-Drain Charge	Q_{gd}		-	0.29	-	
Turn-on Delay Time	$t_{d(on)}$	$V_{GS}=4.5V, V_{DS}=10V, R_L=10\Omega, R_G=6\Omega$	-	54	-	ns
Turn-on Rise Time	t_r		-	104	-	
Turn-off Delay Time	$t_{d(off)}$		-	864	-	
Turn-off Fall Time	t_f		-	474	-	
Input Capacitance	C_{iss}	$V_{GS}=0V, f=1MHz, V_{DS}=10V$	-	55	-	pF
Output Capacitance	C_{DSS}		-	19	-	
Reverse Transfer Capacitance	C_{RSS}		-	12	-	

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RATING AND CHARACTERISTIC CURVES



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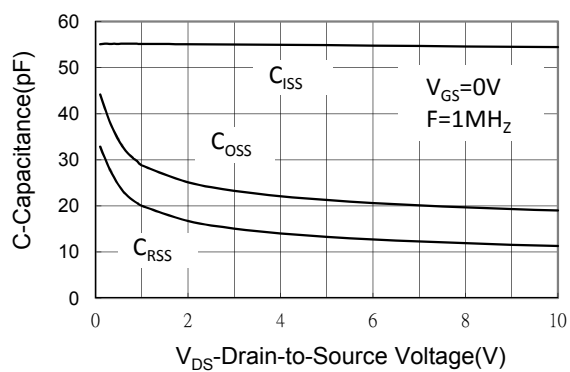


Fig.7 Capacitance

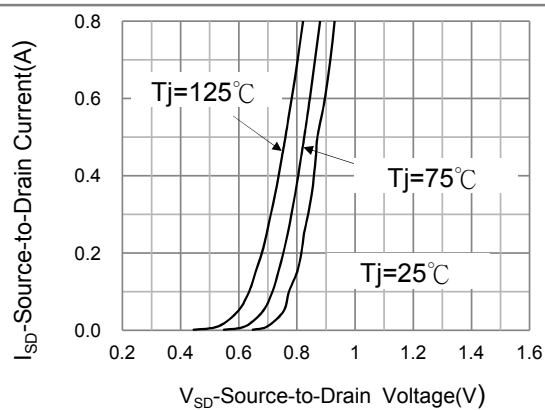
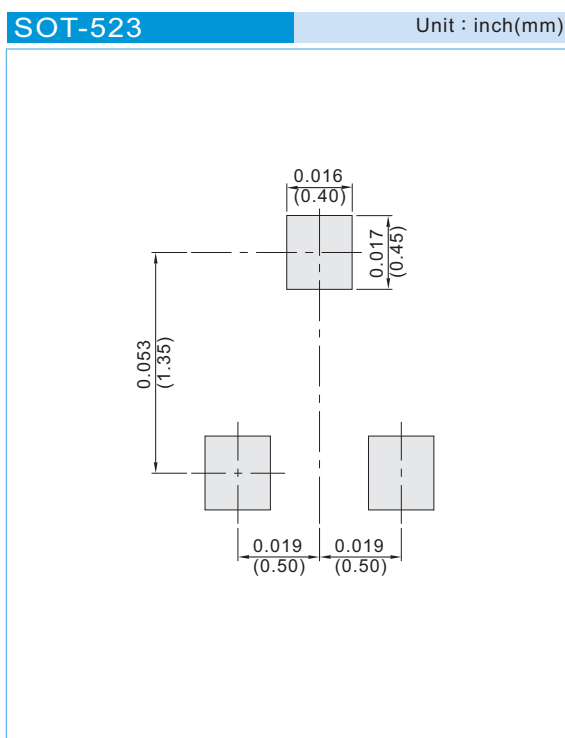


Fig.8 Body Diode Characteristics

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MOUNTING PAD LAYOUT



ORDER INFORMATION

- Packing information

T/R - 4K per 7" plastic Reel

LEGAL STATEMENT

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For example :

RB500V-40_R2_00001



Packing Code XX				Version Code XXXXXX		
Packing type	1 st Code	Packing size code	2 nd Code	HF or RoHS	1 st Code	2 nd ~5 th Code
T/B	A	N/A	0	HF	0	serial number
T/R	R	7"	1	RoHS	1	serial number
B/P	B	13"	2			
T/P	T	26mm	X			
TRR	S	52mm	Y			
TRL	L	PBCU	U			
FORMING	F	PBCD	D			

Part No_packing code_Version

PJE260N02_R1_00001

PJE260N02_R2_00001